**Progress in Applied Surface, Interface**

**and Thin Film Science 2017**

**SURFINT, 20-23. November 2017**

**Invited speakers**  
  
  •**Prof. Hikaru Kobayashi**, Institute of Scientific and Industrial Research,  
     Japan Science and Technology Agency, Osaka University, Japan  
     Surface characteristics of Si nanopowder and its application  
  •**Prof. Dietrich R.T. Zahn**, Technische Universität Chemnitz, Chemnitz, Germany  
     Tip-enhanced Raman Scattering of Semiconducting Nanostructures and 2D Materials  
  •**Prof. Shigeru Masuda**, Graduate School of Arts and Sciences, The University of Tokyo, Japan  
     Local electronic properties at pentacene-metal interface studied by UPS, MAES, and first-principles calculation  
  •**Prof. Vitaly L. Alperovich**, Institute of Semiconductor Physics, Novosibirsk, Russia  
     Photoemission from GaAs(Cs,O) with positive and negative electron affinity  
  •**Prof. Jun Xu**, Nanjing University, Nanjing, China  
     Size-dependent Phosphorus doping effect in nanocrystalline-Si-based multilayers  
  •**Prof. Harri Lipsanen**, Aalto University, Department of Electronics and Nanoengineering, Aalto, Finland  
     Wafer-scale transfer of CVD graphene for flexible electronics  
  •**Dr. Joanna Bauer**, Wroclaw University of Technology, Wroclaw, Poland  
     Antimicrobial Photodynamic Therapy as a potential tool for managing a hospital-acquired infections  
  •**Prof. Marco Fanciulli**, Dipartimento di Scienza dei Materiali, Universita degli Studi di Milano Bicocca,  
     Milano, Italy  
     Investigation of the Si/SiO2 interface in silicon nanowires and its role in donor deactivation  
     and charge transport  
  •**Prof. Kazuyuki Edamoto**, Department of Chemistry, College of Science, Rikkyo University, Tokyo, Japan  
     Surface electronic structures of transition metal phosphides: Soft X-ray photoelectron spectroscopy  
     and X-ray absorption spectroscopy studies  
  •**Prof. Andrea Šagátová**, Faculty of Electrical Engineering and Information Technology,  
     Slovak University of Technology, Bratislava, Slovakia  
     From single GaAs detector to sensor for radiation imaging camera  
  •**Prof. Yossi Paltiel**, Applied Physics Department, Faculty of Science The Hebrew University, Jerusalem, Israel  
  •**Prof. Edmund Dobročka**, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
     Non-conventional scans in high-resolution X-ray diffraction analysis of epitaxial systems  
  •**Prof. Sabu Thomas**, Mahatma Gandhi University, Kerala, India  
     Confinement Effects in Polymer Thin Films  
  •**Prof. Bert Stegemann**, HTW Berlin, University of Applied Sciences, Berlin, Germany  
     Advanced laser and wet-chemical processes for contact preparation in high-efficiency and thin-film solar cells  
  •**Prof. Katsuhiro Akimoto**, Tsukuba University, Tsukuba, Japan  
     Upconversion in NaYF4:Er Nanocrystals by Off-Resonant Excitation  
  •**Prof. Jozef Novák**, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
     Nanorods and Nanocones for Advanced Sensor Applications  
  •**Dr. Dagmar Gregušová**, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
     III-V-based high electron mobility transistor properties influenced by a capping layer modified  
     heterostructure surface  
  •**Dr. Miroslav Mikolášek**, Institute of Electronics and Phototonics,  
     Slovak University of Technology, Bratislava, Slovakia  
     Silicon based MIS photoanodes for solar fuels generation  
  •**Prof. Stanislav Jurečka**, Institute of Aurel Stodola, University of Žilina, Liptovský Mikuláš, Slovakia  
     Investigation of morphological and optical properties of nanostructured layers formed on Si surface  
  •**Prof. Kentaro Imamura**, Institute of Scientific and Industrial Research,  
     Japan Science and Technology Agency, Osaka University, Japan  
     High conversion efficiency black Si solar cells formed by use of surface structure  
     chemical transfer (SSCT) method  
  •**Prof. Alexander Šatka**, Department of Microelectronics, Slovak University of Technology, Bratislava, Slovakia  
     Characterization of advanced GaN structures using CL and EBIC methods  
  •**Dr. Štefan Chromik**, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
     Preparation and study of some two dimensional systems for modern electronics  
  •**Prof. Thomas Chassé**, Institut für Physikalische und Theoretische Chemie, Universität Tübingen, Germany  
     Organic Films for Electronics and Optoelectronics - Reactions, Structures, Interfaces  
  •**Dr. Salvatore A. Lombardo**, Energy Conversion Device Group, CNR-IMM, Italy  
     Performance Instabilities in Amorphous Si Based Solar Cells  
  •**Prof. Ľubica Stuchlíková**, Institute of Electronics and Phototonics, Slovak University of Technology,  
     Bratislava, Slovakia  
     Study of charge capture and emission in perspective semiconductor structures by Deep Level  
     Transient Spectroscopy  
  •**Prof. Nour-eddine Gabouze**, Unite De Development Technologie Silicium, Alger, Algeria  
     Porous silicon membranes for lithium- ion batteries  
  •**Prof. Renato Gonnelli**, Department of Applied Science and Technology, Politecnico di Torino, Italy  
     Electronic phases in ion-gated MoS2 ultrathin layers:  
     Multi-valley superconductivity and possible charge-density wave  
  •**Prof. Dario Daghero**, Department of Applied Science and Technology, Politecnico di Torino, Italy  
     Control of bulk superconductivity by surface charge doping in a BCS superconductor  
  •**Dr. Heike Angermann**, Helmholtz Center Berlin for Materials and Energy, Germany  
     Passivation of crystalline silicon wafers by ultrathin surface oxides prepared in HCl solution  
  •**Dr. Duncan Allsopp**, University of Bath, Department of Electronics and Electrical Engineering, United Kingdom  
     Surface and electrical characterisation of indium-free transparent conducting oxide  
     ohmic contacts on GaN-based light emitting diodes  
  •**Prof. Martin Kopáni**, Faculty of Medicine, Comenius University, Bratislava, Slovakia  
     Effect of etching time on structure of p-type and n-type porous silicon  
  •**Prof. Milan Mikula**, Faculty of chemical and food technology,  
     Slovak University of Technology, Bratislava, Slovakia  
     Study of TiOx hole blocking layers for low-T printable solar cells  
  •**Dr. Yuki Kobayashi**, Institute of Scientific and Industrial Research,  
     Japan Science and Technology Agency, Osaka University, Japan  
     Hydrogen generation by reaction of Si nanopowder with neutral water and medical application  
  •**Dr. Arik Yochelis**, Department of Solar Energy and Environmental Physics, Blaustein Institutes  
     for Desert Research (BIDR)Ben-Gurion University of the Negev, Israel  
     Photo-oxidation on Hematite Electrodes: A Tale of Two Sites  
  •**Dr. Shira Yochelis**, Applied Physics department, Center for Nano Science and Nano Technology  
     the Hebrew University, Edmond J. Safra Campus Givat Ram, Israel  
     Utilizing the Chiral Induced Spin Selective Effect (CISS) to Realize Simple Spintronics Devices